Shigeru Niki

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/4252178/publications.pdf

Version: 2024-02-01

307	8,802	47409	68831
papers	citations	49 h-index	81 g-index

308	308	308	7773
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Impacts of KF Post-Deposition Treatment on the Band Alignment of Epitaxial Cu(In,Ga)Se₂ Heterojunctions. ACS Applied Materials & Interfaces, 2022, 14, 16780-16790.	4.0	3
2	Optical and Structural Properties of High-Efficiency Epitaxial Cu(In,Ga)Se₂ Grown on GaAs. ACS Applied Materials & Interfaces, 2020, 12, 3150-3160.	4.0	11
3	Characterization of Surface and Heterointerface of Cu 2 ZnSn 1â€“ x Ge x Se 4 for Solar Cell Applications. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900708.	1.2	7
4	Current status of transparent conducting oxide layers with high electron mobility and their application in Cu(In,Ga)Se2 mini-modules. Thin Solid Films, 2019, 673, 26-33.	0.8	4
5	Terawatt-scale photovoltaics: Transform global energy. Science, 2019, 364, 836-838.	6.0	320
6	Improving the Open Circuit Voltage through Surface Oxygen Plasma Treatment and 11.7% Efficient Cu₂ZnSnSe₄ Solar Cell. ACS Applied Materials & Interfaces, 2019, 11, 13319-13325.	4.0	36
7	Improved efficiency of Cu(In,Ga)Se₂ miniâ€module via highâ€mobility In₂O₃:W,H transparent conducting oxide layer. Progress in Photovoltaics: Research and Applications, 2019, 27, 491-500.	4.4	16
8	Band Alignment of the CdS/Cu₂Zn(Sn_{1â€“x}Ge_x)Se₄ Heterointerface and Electronic Properties at the Cu₂Zn(Sn_{1â€“x}Ge_x)Se₄ Surface: x = 0, 0.2, and 0.4. ACS Applied Materials & Interfaces, 2019, 11, 4637-4648.	4.0	23
9	Depth Profile of Impurity Phase in Wide-Bandgap Cu(In1â^'x,Gax)Se2 Film Fabricated by Three-Stage Process. Journal of Electronic Materials, 2018, 47, 4944-4949.	1.0	6
10	Reduced recombination in a surface-sulfurized Cu(InGa)Se₂thin-film solar cell. Japanese Journal of Applied Physics, 2018, 57, 055701.	0.8	9
11	Evaluation of femtosecond laser-scribed Cu(In,Ga)Se2 solar cells using scanning spreading resistance microscopy. Applied Physics Express, 2018, 11, 032301.	1.1	10
12	Effect of thermal annealing on the redistribution of alkali metals in Cu(In,Ga)Se2solar cells on glass substrate. Journal of Applied Physics, 2018, 123, 093101.	1.1	14
13	Lithographic fabrication of point contact with Al2O3 rear-surface-passivated and ultra-thin Cu(In,Ga)Se2 solar cells. Thin Solid Films, 2018, 665, 91-95.	0.8	16
14	Effect of Combined Alkali (KFâ€‰+â€‰CsF) Postâ€Deposition Treatment on Cu(InGa)Se₂ Solar Cells. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800372.	1.2	17
15	Single-crystal Cu(In,Ga)Se₂solar cells grown on GaAs substrates. Applied Physics Express, 2018, 11, 082302.	1.1	30
16	Impact of front contact layers on performance of Cu(In,Ga)Se₂ solar cells in relaxed and metastable states. Progress in Photovoltaics: Research and Applications, 2018, 26, 789-799.	4.4	11
17	Significance of metastable acceptors in Cu(In,Ga)Se₂ solar cells in accelerated lifetime testing. Japanese Journal of Applied Physics, 2018, 57, 092301.	0.8	7
18	Deep level emission in polycrystalline CuGaSe₂ thin-films observed by micro-photoluminescence. Japanese Journal of Applied Physics, 2018, 57, 08RC02.	0.8	2

#	Article	IF	Citations
19	Ultrafast laser scribing of transparent conductive oxides in Cu(In,Ga)Se₂ solar cells via laser lift-off process: the control of laser-induced damage. Proceedings of SPIE, 2017, , .	0.8	2
20	Terawatt-scale photovoltaics: Trajectories and challenges. Science, 2017, 356, 141-143.	6.0	303
21	Band Alignment of CdS/Cu2ZnSnSe4 Heterointerface and Solar Cell Performances. MRS Advances, 2017, 2, 3157-3162.	0.5	3
22	Electronic structures of Cu₂ZnSnSe₄surface and CdS/Cu₂ZnSnSe₄heterointerface. Japanese Journal of Applied Physics, 2017, 56, 065701.	0.8	7
23	Improved performance in Cu2ZnSnSe4 solar cells using a sandwich-structured ZnSe/Cu2SnSe3/ZnSe precursor. Current Applied Physics, 2017, 17, 366-369.	1.1	5
24	Cu(In,Ga)Se₂ Solar Cells with Amorphous In₂O₃-Based Front Contact Layers. ACS Applied Materials & Interfaces, 2017, 9, 29677-29686.	4.0	14
25	Improvement of minority carrier lifetime and conversion efficiency by Na incorporation in Cu2ZnSnSe4 solar cells. Journal of Applied Physics, 2017, 122, .	1.1	37
26	Effects of long-term heat-light soaking on Cu(In,Ga)Se₂ solar cells with KF postdeposition treatment. Applied Physics Express, 2017, 10, 092301.	1.1	51
27	Electronic structure of Cu₂ZnSn(S_xSe_{1â^'x})₄ surface and CdS/Cu₂ZnSn(S_xSe_{1â^'x})₄ interface. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, .	0.8	9
28	Degradation mechanism of Cu(In,Ga)Se₂ solar cells induced by exposure to air. Japanese Journal of Applied Physics, 2016, 55, 072301.	0.8	10
29	Quantitative determination of optical and recombination losses in thin-film photovoltaic devices based on external quantum efficiency analysis. Journal of Applied Physics, 2016, 120, .	1.1	105
30	A comparative study on charge carrier recombination across the junction region of Cu2ZnSn(S,Se)4 and Cu(In,Ga)Se2 thin film solar cells. AIP Advances, 2016, 6, .	0.6	10
31	Effect of pre-annealing on Cu2ZnSnSe4 thin-film solar cells prepared from stacked Zn/Cu/Sn metal precursors. Materials Letters, 2016, 176, 78-82.	1.3	7
32	Improvement of voltage deficit of Ge-incorporated kesterite solar cell with 12.3% conversion efficiency. Applied Physics Express, 2016, 9, 102301.	1.1	129
33	Structure of chemically deposited Zn(S,O,OH) buffer layer and the effects on the performance of Cu(in,Ga)Se₂ solar cell. Progress in Photovoltaics: Research and Applications, 2016, 24, 397-404.	4.4	8
34	Comparison of ZnO:B and ZnO:Al layers for Cu(In,Ga)Se2 submodules. Thin Solid Films, 2016, 614, 79-83.	0.8	18
35	Effects of Mo surface oxidation on Cu(In,Ga)Se₂ solar cells fabricated by three-stage process with KF postdeposition treatment. Japanese Journal of Applied Physics, 2016, 55, 022304.	0.8	15
36	Ge-incorporated Cu2ZnSnSe4 thin-film solar cells with efficiency greater than 10%. Solar Energy Materials and Solar Cells, 2016, 144, 488-492.	3.0	95

#	Article	IF	Citations
37	Femtosecond Laser Scribing of Cu(In,Ga)Se2 Thin-Film Solar Cell. Journal of Laser Micro Nanoengineering, 2016, 11, 130-136.	0.4	4
38	Characterization of Electron-Induced Defects in Cu (In, Ga) Se2 Thin Films by Photoluminescence. Materials Research Society Symposia Proceedings, 2015, 1771, 157-161.	0.1	0
39	Compositional dependence photoluminescence study of polycrystalline CuGaSe2 thin films. , 2015, , .		1
40	Electrical performance of the InGaP solar cell irradiated with low energy electron beams. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 773-776.	0.8	4
41	Optical constants of Cu(In, Ga)Se2 for arbitrary Cu and Ga compositions. Journal of Applied Physics, 2015, 117, .	1.1	53
42	Cu(In,Ga)Se₂ Solar Cells With Amorphous Oxide Semiconducting Buffer Layers. IEEE Journal of Photovoltaics, 2015, 5, 956-961.	1.5	26
43	Narrow-bandgap Cu2Sn1â^'xGexSe3 thin film solar cells. Materials Letters, 2015, 158, 205-207.	1.3	21
44	Study of time-resolved photoluminescence in Cu₂ZnSn(S,Se)₄thin films with different Cu/Sn ratio. Japanese Journal of Applied Physics, 2015, 54, 08KC15.	0.8	4
45	Wide-gap solar cells using a novel ZnCuGaSe₂absorber. Japanese Journal of Applied Physics, 2015, 54, 08KC17.	0.8	0
46	Investigation of the properties of deep-level defect in Cu(In,Ga)Se₂thin films by steady-state photocapacitance and time-resolved photoluminescence measurements. Japanese Journal of Applied Physics, 2015, 54, 04DR02.	0.8	5
47	Dielectric functions of Cu2ZnSnSe4 and Cu2SnSe3 semiconductors. Journal of Applied Physics, 2015, 117, 015702.	1.1	40
48	Potential-induced degradation of Cu(In,Ga)Se₂photovoltaic modules. Japanese Journal of Applied Physics, 2015, 54, 08KC13.	0.8	64
49	Determination of deep-level defects in Cu2ZnSn(S,Se)4 thin-films using photocapacitance method. Applied Physics Letters, 2015, 106, .	1.5	20
50	Investigation of InGaP/(In)AlGaAs/GaAs triple-junction top cells for smart stacked multijunction solar cells grown using molecular beam epitaxy. Japanese Journal of Applied Physics, 2015, 54, 08KE02.	0.8	6
51	Study of Cu2ZnSn(S,Se)4Thin Films for Solar Cell Application. Journal of Physics: Conference Series, 2015, 596, 012019.	0.3	2
52	Improvement of In2 S3 /ZnCuInS2 interfaces for wide-gap solar cells. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 769-772.	0.8	1
53	Degradation of Cu(In, Ga)Se 2 thin-film solar cells due to the ionization effect of low-energy electrons. Thin Solid Films, 2015, 582, 91-94.	0.8	3
54	Individual identification of free hole and electron dynamics in CuIn1â^'xGaxSe2 thin films by simultaneous monitoring of two optical transitions. Applied Physics Letters, 2015, 106, .	1.5	4

#	Article	IF	Citations
55	Cu₂ZnSnSe₄thin-film solar cells fabricated using Cu₂SnSe₃and ZnSe bilayers. Applied Physics Express, 2015, 8, 042301.	1.1	21
56	Effects of alkali-metal block layer to enhance Na diffusion into Cu(in,Ga)Se2 absorber on flexible solar cells. Solar Energy Materials and Solar Cells, 2015, 133, 21-25.	3.0	12
57	Characterization of electronic structure of Cu2ZnSn(S Se1â^')4 absorber layer and CdS/Cu2ZnSn(S) Tj ETQq1 1 0.784314 rgBT /Overlo 2015, 582, 166-170.	0.8	31
58	Study of recombination process in Cu<inf>2</inf>ZnSnS<inf>4</inf> thin film using two-wavelength excited photoluminescence. , 2014, , .		2
59	Radiation response of the fill-factor for GaAs solar cells with InGaAs quantum dot layers. , 2014, , .		2
60	Characterization of electronic structure of oxysulfide buffers and band alignment at buffer/absorber interfaces in Cu(In,Ga)Se₂-based solar cells. Japanese Journal of Applied Physics, 2014, 53, 05FW09.	0.8	9
61	Effects of the Morphology of Chemically Deposited Zn(O,S) Buffer Layers on the Performance Cu(In,Ga)Se2 Solar Cell. Energy Procedia, 2014, 60, 43-47.	1.8	6
62	Influence of electron irradiation on electroluminescence of Cu(In,Ga)Se₂solar cells. Japanese Journal of Applied Physics, 2014, 53, 05FW08.	0.8	9
63	Structural tuning of wide-gap chalcopyrite CuGaSe₂ thin films and highly efficient solar cells: differences from narrow-gap Cu(In,Ga)Se₂. Progress in Photovoltaics: Research and Applications, 2014, 22, 821-829.	4.4	61
64	Buried p-n junction formation in CuGaSe₂ thin-film solar cells. Applied Physics Letters, 2014, 104, 031606.	1.5	27
65	Temperature induced phase transformation in coevaporated Cu2SnSe3 thin films. Materials Letters, 2014, 116, 61-63.	1.3	12
66	Composition control of Cu2ZnSnSe4-based solar cells grown by coevaporation. Thin Solid Films, 2014, 551, 27-31.	0.8	21
67	MBE-grown InGaP/GaAs/InGaAsP triple junction solar cells fabricated by advanced bonding technique. , 2014, , .		2
68	Investigation of deep-level defects in Cu(In,Ga)Se2 thin films by a steady-state photocapacitance method. Journal of Applied Physics, 2014, 116, 163703.	1.1	4
69	InGaP/GaAs tandem solar cells fabricated using solid-source molecular beam epitaxy. Japanese Journal of Applied Physics, 2014, 53, 05FV06.	0.8	17
70	Quantitative Assessment of Optical Gain and Loss in Submicron-Textured<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">C</mml:mi><mml:mi mathvariant="normal">u</mml:mi><mml:mi mathvariant="normal">I</mml:mi><mml:msub><mml:mrow><mml:mi mathvariant="normal">n</mml:mi></mml:mrow><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></	1.5	67
71	Physical Review<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">CuIn</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^'</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi>x</mml:mi></mml:msub></mml:math><mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">Se</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math> Physical Review	1.1	21
72	Interfacial Alkali Diffusion Control in Chalcopyrite Thin-Film Solar Cells. ACS Applied Materials & Interfaces, 2014, 6, 14123-14130.	4.0	23

#	Article	IF	Citations
73	Investigation of the relative density of deep defects in Cu(In,Ga)Se2 thin films dependent on Ga content by transient photocapacitance method. Japanese Journal of Applied Physics, 2014, 53, 068008.	0.8	12
74	Texture and morphology variations in (In,Ga)₂Se₃ and Cu(In,Ga)Se₂ thin films grown with various Se source conditions. Progress in Photovoltaics: Research and Applications, 2013, 21, 544-553.	4.4	36
75	InGaAs quantum dot superlattice with vertically coupled states in InGaP matrix. Journal of Applied Physics, 2013, 114, .	1.1	17
76	Impact of Se flux on the defect formation in polycrystalline Cu(In,Ga)Se2 thin films grown by three stage evaporation process. Journal of Applied Physics, 2013, 113, 064907.	1.1	15
77	Impact of a binary Ga2Se3 precursor on ternary CuGaSe2 thin-film and solar cell device properties. Applied Physics Letters, 2013, 103, .	1.5	24
78	In(Ga)As quantum dots on InGaP layers grown by solid-source molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 430-434.	0.7	17
79	Characterization of Cu(In,Ga)Se2 grown by MBE by two-wavelength excited photoluminescence spectroscopy. Journal of Crystal Growth, 2013, 378, 162-164.	0.7	11
80	Investigation of deep-level defects in Cu(In,Ga)Se2 thin films by two-wavelength excitation photo-capacitance spectroscopy. Applied Physics Letters, 2013, 103, 163905.	1.5	12
81	Growth and characterization of coevaporated Cu2SnSe3 thin films for photovoltaic applications. Thin Solid Films, 2013, 536, 111-114.	0.8	49
82	Highly Efficient Cu(In,Ga)Se₂Thin-Film Submodule Fabricated Using a Three-Stage Process. Applied Physics Express, 2013, 6, 112303.	1.1	15
83	Miniband formation in InGaAs quantum dot superlattice with InGaP matrix for application to intermediate-band solar cells. , 2013, , .		2
84	Influence of electrical performance on Cu-related defects generated by 250keV electron irradiation in Cu (In, Ga) Se2 thin-film solar cells. Thin Solid Films, 2013, 535, 353-356.	0.8	21
85	Cu(In,Ga)Se2 solar cells and mini-modules fabricated on thin soda-lime glass substrates. Solar Energy Materials and Solar Cells, 2013, 119, 163-168.	3.0	19
86	InGaP solar cells fabricated using solid-source molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 576-578.	0.7	27
87	Dielectric function of Cu(In, Ga)Se2-based polycrystalline materials. Journal of Applied Physics, 2013, 113, .	1.1	98
88	Change in the electrical performance of GaAs solar cells with InGaAs quantum dot layers by electron irradiation. Solar Energy Materials and Solar Cells, 2013, 108, 263-268.	3.0	14
89	Monolithically integrated flexible Cu(In,Ga)Se2 solar cells and submodules using newly developed structure metal foil substrate with a dielectric layer. Solar Energy Materials and Solar Cells, 2013, 112, 106-111.	3.0	26
90	Over 20% Efficiency Mechanically Stacked Multi-Junction Solar Cells Fabricated by Advanced Bonding Using Conductive Nanoparticle Alignments. Materials Research Society Symposia Proceedings, 2013, 1538, 167-171.	0.1	10

#	Article	IF	Citations
91	Characterization of Electron-Induced Defects in Cu (In, Ga) Se2 Thin-Film Solar Cells using Electroluminescence. Materials Research Society Symposia Proceedings, 2013, 1538, 27-32.	0.1	1
92	Observation of Sodium Diffusion in CIGS Solar Cells with Mo/TCO/Mo Hybrid Back Contacts. Materials Research Society Symposia Proceedings, 2013, 1538, 61-66.	0.1	2
93	Electrical performance degradation of GaAs solar cells with InGaAs quantum dot layers due to proton irradiation. , 2013, , .		3
94	Correlation between Electrical Properties and Crystal c-Axis Orientation of Zinc Oxide Transparent Conducting Films. Japanese Journal of Applied Physics, 2012, 51, 10NC16.	0.8	2
95	Fabrication and Characterization of Wide-Gap ZnCuInS$_{2}$ Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10NC06.	0.8	1
96	Fabrication and Characterization of Cu(In,Ga)(S,Se)$_{2}$-Based Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10NC04.	0.8	1
97	InGaP-based InGaAs quantum dot solar cells with GaAs spacer layer fabricated using solid-source molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	1.5	32
98	Highâ€efficiency CIGS submodules. Progress in Photovoltaics: Research and Applications, 2012, 20, 595-599.	4.4	14
99	Ultra-high stacks of InGaAs/GaAs quantum dots for high efficiency solar cells. Energy and Environmental Science, 2012, 5, 6233.	15.6	75
100	Fabrication and Characterization of Cu(In,Ga)(S,Se)2-Based Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10NC04.	0.8	2
101	Impact of Cu/III ratio on the near-surface defects in polycrystalline CuGaSe2 thin films. Applied Physics Letters, 2011, 98, 112105.	1.5	18
102	Monolithically integrated CIGS sub-modules fabricated on new-structured flexible substrates. , 2011, , .		4
103	Ultra-high stacks of InGaAs quantum dots for high efficiency solar cells. , 2011, , .		2
104	Local Structure around Dopant Site in Ga-Doped ZnO from Extended X-ray Absorption Fine Structure Measurements. Journal of the Physical Society of Japan, 2011, 80, 074602.	0.7	5
105	Tunnel current through a miniband in InGaAs quantum dot superlattice solar cells. Solar Energy Materials and Solar Cells, 2011, 95, 2920-2923.	3.0	24
106	CIGS thin films, solar cells, and submodules fabricated using a rf-plasma cracked Se-radical beam source. Thin Solid Films, 2011, 519, 7216-7220.	0.8	15
107	Thickness study of Al:ZnO film for application as a window layer in Cu(In1â^'xGax)Se2 thin film solar cell. Applied Surface Science, 2011, 257, 4026-4030.	3.1	67
108	Development of high-efficiency CIGS integrated submodules using in-line deposition technology. Solar Energy Materials and Solar Cells, 2011, 95, 254-256.	3.0	25

#	Article	IF	Citations
109	Determination of Cu(In1â^'xGax)3Se5 defect phase in MBE grown Cu(In1â^'xGax)Se2 thin film by Rietveld analysis. Solar Energy Materials and Solar Cells, 2011, 95, 231-234.	3.0	15
110	Dependence of Se beam pressure on defect states in CIGS-based solar cells. Solar Energy Materials and Solar Cells, 2011, 95, 227-230.	3.0	34
111	Multi-stacked quantum dot solar cells fabricated by intermittent deposition of InGaAs. Solar Energy Materials and Solar Cells, 2011, 95, 163-166.	3.0	56
112	Cu-dependent phase transition in polycrystalline CuGaSe2 thin films grown by three-stage process. Journal of Applied Physics, 2011, 110, 014903.	1.1	8
113	Time-Resolved Microphotoluminescence Study of Cu(In,Ga)Se₂. Japanese Journal of Applied Physics, 2011, 50, 05FC01.	0.8	18
114	Time-Resolved Microphotoluminescence Study of Cu(In,Ga)Se₂. Japanese Journal of Applied Physics, 2011, 50, 05FC01.	0.8	25
115	Recent Developments in Chalcopyrite Solar Cell and Module Technologies. Journal of the Vacuum Society of Japan, 2010, 53, 25-29.	0.3	0
116	Development of high-efficiency flexible Cu(In,Ga)Se2 solar cells: A study of alkali doping effects on CIS, CIGS, and CGS using alkali-silicate glass thin layers. Current Applied Physics, 2010, 10, S154-S156.	1.1	53
117	Formation of ionic bonds between a fatty-acid Langmuirâ€"Blodgett monolayer and a zinc oxide substrate. Journal of Colloid and Interface Science, 2010, 352, 299-302.	5.0	1
118	Characterization of Zn1â^'xMgxO transparent conducting thin films fabricated by multi-cathode RF-magnetron sputtering. Thin Solid Films, 2010, 518, 2949-2952.	0.8	34
119	Monolithically integrated flexible Cu(In,Ga)Se2 solar cell submodules. Solar Energy Materials and Solar Cells, 2010, 94, 2052-2056.	3.0	34
120	CIGS absorbers and processes. Progress in Photovoltaics: Research and Applications, 2010, 18, 453-466.	4.4	403
121	Two-dimensional polaron mass in ZnO quantum Hall systems. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1599-1601.	0.8	8
122	Highly stacked InGaAs quantum dot structures grown with two species of As. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3C4-C3C8.	0.6	19
123	Characteristics of highly stacked quantum dot solar cells fabricated by intermittent deposition of InGaAs. , 2010, , .		3
124	Change in the electrical performance of InGaAs quantum dot solar cells due to irradiation. , 2010, , .		3
125	Highly Stacked and High-Quality Quantum Dots Fabricated by Intermittent Deposition of InGaAs. Japanese Journal of Applied Physics, 2010, 49, 030211.	0.8	24
126	Formation of Hexagonal Pyramids and Pits on V-/VI-Polar and III-/II-Polar GaN/ZnO Surfaces by Wet Etching. Journal of the Electrochemical Society, 2010, 157, D60.	1.3	46

#	Article	IF	Citations
127	Miniband formation in InGaAs quantum dot superlattice. Applied Physics Letters, 2010, 97, .	1.5	41
128	Highly stacked and well-aligned In0.4Ga0.6As quantum dot solar cells with In0.2Ga0.8As cap layer. Applied Physics Letters, 2010, 97, 183104.	1.5	50
129	Monolithically integrated CIGS submodules fabricated on flexible substrates. , 2010, , .		2
130	Flexible Cu(In,Ga)Se2 solar cells fabricated using alkali-silicate glass thin layers as an alkali source material. Journal of Renewable and Sustainable Energy, 2009, 1, 013102.	0.8	38
131	Optical dielectric constant inhomogeneity along the growth axis in ZnO-based transparent electrodes deposited on glass substrates. Journal of Applied Physics, 2009, 105, .	1.1	14
132	Temperature dependence of photocapacitance spectrum of CIGS thin-film solar cell. Thin Solid Films, 2009, 517, 2403-2406.	0.8	33
133	CIGS solar cell with CdS buffer layer deposited by ammoniaâ€free process. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1072-1075.	0.8	10
134	Effects of Mo back contact thickness on the properties of CIGS solar cells. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1063-1066.	0.8	25
135	High sensitivity and wide bandwidth image sensor using CuIn1â^'xGaxSe2 thin films. Thin Solid Films, 2009, 517, 2392-2394.	0.8	7
136	Infrared reflectionâ€“absorption spectroscopy applied to a merocyanine dye J-aggregate deposited on transparent electrodes based on zinc oxide. Thin Solid Films, 2009, 518, 462-465.	0.8	6
137	Large grain Cu(In,Ga)Se2 thin film growth using a Se-radical beam source. Solar Energy Materials and Solar Cells, 2009, 93, 792-796.	3.0	24
138	CIGS solar cell with MBE-grown ZnS buffer layer. Solar Energy Materials and Solar Cells, 2009, 93, 970-972.	3.0	130
139	Fabrication of homojunction GaInNAs solar cells by atomic hydrogen-assisted molecular beam epitaxy. Solar Energy Materials and Solar Cells, 2009, 93, 1120-1123.	3.0	10
140	Effect of Se/(Ga+In) ratio on MBE grown Cu(In,Ga)Se2 thin film solar cell. Journal of Crystal Growth, 2009, 311, 2212-2214.	0.7	40
141	Zn1â^'xMgxO/ZnO heterostructures studied by Kelvin probe force microscopy conjunction with probe characterizer. Applied Surface Science, 2009, 256, 1180-1183.	3.1	0
142	Band profiles of ZnMgO/ZnO heterostructures confirmed by Kelvin probe force microscopy. Applied Physics Letters, 2009, 94, .	1.5	32
143	Na-induced variations in the structural, optical, and electrical properties of Cu(In,Ga)Se2 thin films. Journal of Applied Physics, 2009, 106, .	1.1	148
144	Efficiency enhancement of flexible CIGS solar cells using alkali-silicate glass thin layers as an alkali source material. , 2009, , .		3

#	Article	IF	Citations
145	Effects of annealing under various atmospheres on electrical properties of Cu(In,Ga)Se2 films and CdS/Cu(In,Ga)Se2 heterostructures. Thin Solid Films, 2008, 516, 7036-7040.	0.8	24
146	Alkali incorporation control in Cu(In,Ga)Se2 thin films using silicate thin layers and applications in enhancing flexible solar cell efficiency. Applied Physics Letters, 2008, 93, .	1.5	71
147	Polarization-induced two-dimensional electron gases in ZnMgO/ZnO heterostructures. Applied Physics Letters, 2008, 93, .	1.5	131
148	Photoluminescence Analysis of Proton Irradiation Effects in Cu(In,Ga)Se₂ Solar Cells. Japanese Journal of Applied Physics, 2008, 47, 857.	0.8	10
149	Study of Band Alignment at CBD-CdS/Cu(In_{1-x}Ga_x)Se₂ (x = 0.2 - 1.0) Interfaces by Photoemission and Inverse Photoemission Spectroscopy. Materials Research Society Symposia Proceedings, 2007, 1012, 1.	0.1	6
150	Formation of two-dimensional electron gas and enhancement of electron mobility by Zn polar ZnMgO/ZnO heterostructures. , 2007, 6474, 78.		0
151	Study of Band Alignment at the Interface between CBD-CdS and CIGS grown by H2O-introduced co-evaporation. Materials Research Society Symposia Proceedings, 2007, 1012, 1.	0.1	0
152	Growth of polycrystalline Cu(In,Ga)Se2 thin films using a radio frequency-cracked Se-radical beam source and application for photovoltaic devices. Applied Physics Letters, 2007, 91, .	1.5	29
153	Strong excitonic transition of Zn1â^'xMgxO alloy. Applied Physics Letters, 2007, 91, .	1.5	55
154	Photoluminescence characterization of Zn1â^'xMgxO epitaxial thin films grown on ZnO by radical source molecular beam epitaxy. Applied Physics Letters, 2007, 90, 124104.	1.5	49
155	Oblique-Incidence Infrared Reflection in Thin ZnO Films Deposited on Sapphire by Gas-Source MBE. AIP Conference Proceedings, 2007, , .	0.3	3
156	Junction formation of CuInSe2 with CdS: A comparative study of â€œdryâ€•and â€œwetâ€•interfaces. Thin Solid Films, 2007, 515, 6112-6118.	0.8	22
157	Characteristics of scattered laser light signals from Cu(In,Ga)Se2 films. Thin Solid Films, 2007, 515, 6222-6225.	0.8	3
158	High electron mobility Zn polar ZnMgO/ZnO heterostructures grown by molecular beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 358-361.	0.7	33
159	Investigation of relation between Ga concentration and defect levels of Al/Cu(In,Ga)Se2 Schottky junctions using admittance spectroscopy. Thin Solid Films, 2007, 515, 6208-6211.	0.8	6
160	Control of the thin film properties of Cu(In,Ga)Se2 using water vapor introduction during growth. Journal of Applied Physics, 2006, 100, 096106.	1.1	11
161	Determination of crystallographic polarity of ZnO bulk crystals and epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1018-1021.	0.8	5
162	Photoluminescence recombination centers in ZnO. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1026-1029.	0.8	0

#	Article	IF	Citations
163	Study on electrical properties of Al/Cu(In,Ga)Se2 Schottky junction and ZnO/CdS/Cu(In,Ga)Se2 heterojunction using admittance spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2576-2580.	0.8	2
164	Rump Session: Science and technologies which support production of CIS solar cells and modules. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2585-2587.	0.8	0
165	Effects of water vapor introduction during Cu(In1-xGax)Se2deposition on thin film properties and solar cell performance. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2609-2614.	0.8	4
166	Crystallographic growth orientation of Cu(InGa)Se2films in relation to substrate material nature. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2639-2643.	0.8	6
167	Soft X-ray XANES of N in ZnO:N â€“ Why is doping so difficult?. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 75-78.	0.6	15
168	Negative thermal quenching of photoluminescence in ZnO. Physica B: Condensed Matter, 2006, 376-377, 711-714.	1.3	46
169	Structural changes of CIGS during deposition investigated by spectroscopic light scattering: A study on Ga concentration and Se pressure. Solar Energy Materials and Solar Cells, 2006, 90, 3377-3384.	3.0	6
170	Two-dimensional electron gas in Zn polar ZnMgOâˆ•ZnO heterostructures grown by radical source molecular beam epitaxy. Applied Physics Letters, 2006, 89, 132113.	1.5	118
171	Microstructural Evolution of ZnO by Wet-Etching Using Acidic Solutions. Journal of Nanoscience and Nanotechnology, 2006, 6, 3364-3368.	0.9	13
172	Ohmic Contact to Phosphorous-Doped ZnO Using Ptâˆ•Niâˆ•Au for p-n Homojunction Diode. Journal of the Electrochemical Society, 2006, 153, G1047.	1.3	8
173	Direct Observation of Nitrogen Location in Molecular Beam Epitaxy Grown Nitrogen-Doped ZnO. Physical Review Letters, 2006, 96, 045504.	2.9	119
174	XAFS Observations of Initial Growth of 0001 ZnO on Sapphire Substrates. Physica Scripta, 2005, , 523.	1.2	0
175	The effects of thermal treatments on the electrical properties of phosphorus doped ZnO layers grown by MBE. Journal of Crystal Growth, 2005, 278, 268-272.	0.7	33
176	Piezoelectric photothermal investigation of proton irradiation induced defects in CuInSe2 epitaxial films. Thin Solid Films, 2005, 480-481, 250-253.	0.8	6
177	Improvement of ZnO TCO film growth for photovoltaic devices by reactive plasma deposition (RPD). Thin Solid Films, 2005, 480-481, 199-203.	0.8	57
178	Characterization of interface nature and band alignment in CBD-CdS/Cu(In,Ga)Se2 bi-layer structure by photoemission and inverse photoemission spectroscopy. Thin Solid Films, 2005, 480-481, 183-187.	0.8	43
179	Structural changes of CuGaSe2 films during the three-stage process observed by spectroscopic light scattering. Thin Solid Films, 2005, 480-481, 367-372.	0.8	2
180	SXPS investigation of the Cd partial electrolyte treatment of CuInSe2 absorbers. Thin Solid Films, 2005, 480-481, 218-223.	0.8	15

#	Article	IF	Citations
181	Fabrication of wide-gap Cu(In1âˆ'xGax)Se2 thin film solar cells: a study on the correlation of cell performance with highly resistive i-ZnO layer thickness. Solar Energy Materials and Solar Cells, 2005, 87, 541-548.	3.0	108
182	Growth of ZnO and device applications. Applied Surface Science, 2005, 244, 504-510.	3.1	32
183	A Study of the Diffusion and pn-Junction Formation in CIGS Solar Cells using EBIC and EDX Measurements. Materials Research Society Symposia Proceedings, 2005, 865, 631.	0.1	4
184	Shallow donor generation in ZnO by remote hydrogen plasma. Journal of Electronic Materials, 2005, 34, 399-403.	1.0	12
185	Properties of Cu(In,Ga)Se2:Fe Thin Films For Solar Cells. Materials Research Society Symposia Proceedings, 2005, 865, 14121.	0.1	8
186	Built-in Potential and Open Circuit Voltage of Heterojunction CuIn_{1-x}GaxSe₂ Solar Cells. Materials Research Society Symposia Proceedings, 2005, 865, 5191.	0.1	7
187	Excitation-Power Dependence of Free Exciton Photoluminescence of Semiconductors. Japanese Journal of Applied Physics, 2005, 44, 6113-6114.	0.8	48
188	Photoluminescence characterization of excitonic centers in ZnO epitaxial films. Applied Physics Letters, 2005, 86, 221907.	1.5	22
189	Progress in the Efficiency of Wide-Gap Cu(In1-xGax)Se2Solar Cells Using CIGSe Layers Grown in Water Vapor. Japanese Journal of Applied Physics, 2005, 44, L679-L682.	0.8	32
190	Effect of Rapid Thermal Annealing on Al Dopedn-ZnO Films Grown by RF-Magnetron Sputtering. Japanese Journal of Applied Physics, 2005, 44, 4776-4779.	0.8	56
191	Determination of crystallographic polarity of ZnO layers. Applied Physics Letters, 2005, 87, 141904.	1.5	63
192	High electron concentration and mobility in Al-doped n-ZnO epilayer achieved via dopant activation using rapid-thermal annealing. Journal of Applied Physics, 2005, 97, 066103.	1.1	106
193	Remote hydrogen plasma doping of single crystal ZnO. Applied Physics Letters, 2004, 84, 2545-2547.	1.5	124
194	Degenerate layers in epitaxial ZnO films grown on sapphire substrates. Applied Physics Letters, 2004, 84, 4412-4414.	1.5	65
195	Proton-beam-induced defect levels in CuInSe2 thin-film absorbers: An investigation on nonradiative electron transitions. Applied Physics Letters, 2004, 85, 1347-1349.	1.5	3
196	Improved External Efficiency InGaN-Based Light-Emitting Diodes with Transparent Conductive Ga-Doped ZnO as p-Electrodes. Japanese Journal of Applied Physics, 2004, 43, L180-L182.	0.8	59
197	Doping properties of ZnO thin films for photovoltaic devices grown by URT-IP (ion plating) method. Thin Solid Films, 2004, 451-452, 219-223.	0.8	25
198	InGaN-based light-emitting diodes fabricated with transparent Ga-doped ZnO as ohmicp-contact. Physica Status Solidi A, 2004, 201, 2704-2707.	1.7	13

#	Article	IF	Citations
199	In situ diagnostic methods for thin-film fabrication: utilization of heat radiation and light scattering. Progress in Photovoltaics: Research and Applications, 2004, 12, 219-234.	4.4	57
200	Thermal processing induced structural changes in ZnO films grown on (11&2macr;0) sapphire substrates using molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 868-871.	0.8	0
201	Characterization of ZnO crystals by photoluminescence spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 872-875.	0.8	22
202	Effects of low temperature buffer layer treatments on the growth of high quality ZnO films. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 888-891.	0.8	9
203	Polycrystalline n -ZnO/p -Cu2 O heterojunctions grown by RF-magnetron sputtering. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1067-1070.	0.8	63
204	Proton irradiation damages in CuInSe2 thin film solar cell materials by a piezoelectric photothermal spectroscopy. Solid-State Electronics, 2004, 48, 1815-1818.	0.8	9
205	An option for the surface science on Cu chalcopyrites: the selenium capping and decapping process. Surface Science, 2004, 557, 263-268.	0.8	21
206	Effect of band offset on the open circuit voltage of heterojunction CuIn1â^'xGaxSe2 solar cells. Applied Physics Letters, 2004, 85, 5607-5609.	1.5	38
207	Band-gap modified Al-doped Zn1â^'xMgxO transparent conducting films deposited by pulsed laser deposition. Applied Physics Letters, 2004, 85, 1374-1376.	1.5	131
208	Photoemission study and band alignment of the CuInSe2(001)/CdS heterojunction. Applied Physics Letters, 2004, 84, 3067-3069.	1.5	47
209	An EXAFS and XANES study of MBE grown Cu-doped ZnO. Nuclear Instruments & Methods in Physics Research B, 2003, 199, 190-194.	0.6	25
210	Properties of CuInGaSe2 solar cells based upon an improved three-stage process. Thin Solid Films, 2003, 431-432, 6-10.	0.8	30
211	In situ deposition rate monitoring during the three-stage-growth process of Cu(In,Ga)Se2 absorber films. Thin Solid Films, 2003, 431-432, 16-21.	0.8	18
212	ZnO transparent conducting films deposited by pulsed laser deposition for solar cell applications. Thin Solid Films, 2003, 431-432, 369-372.	0.8	237
213	Electron beam probe quantization of compound composition: surface phases and surface roughness. Thin Solid Films, 2003, 431-432, 277-283.	0.8	12
214	Natural ordering of ZnO1â^'xSex grown by radical source MBE. Journal of Crystal Growth, 2003, 251, 633-637.	0.7	5
215	The chemical environment about Cd atoms in Cd chemical bath treated CuInSe2 and CuGaSe2. Journal of Physics and Chemistry of Solids, 2003, 64, 1733-1735.	1.9	5
216	Adjusting the sodium diffusion into CuInGaSe2 absorbers by preheating of Mo/SLG substrates. Journal of Physics and Chemistry of Solids, 2003, 64, 1877-1880.	1.9	12

#	Article	IF	Citations
217	Growth and electrical properties of ZnO thin films deposited by novel ion plating method. Thin Solid Films, 2003, 445, 274-277.	0.8	51
218	Cu(In1â^'xGax)Se2 growth studies by in situ spectroscopic light scattering. Applied Physics Letters, 2003, 82, 2091-2093.	1.5	43
219	Estimation and Correction Procedure for the Effects of Surface Roughness on Electron Probe Microanalysis. Japanese Journal of Applied Physics, 2003, 42, 5811-5812.	0.8	1
220	Point Defect Changes in CuGaSe2 Induced by Gas Annealing. Materials Research Society Symposia Proceedings, 2003, 763, 5171.	0.1	3
221	Observation of Exciton-Polariton Emissions from a ZnO Epitaxial Film on the a-Face of Sapphire Grown by Radical-Source Molecular-Beam-Epitaxy. Japanese Journal of Applied Physics, 2002, 41, L935-L937.	0.8	19
222	Photoreflectance and Photoluminescence of Exciton-Polaritons in a ZnO Epilayer Grown on the a-Face of Sapphire by Radical-Source Molecular-Beam Epitaxy. Physica Status Solidi A, 2002, 192, 171-176.	1.7	7
223	Room-temperature deposition of Al-doped ZnO films by oxygen radical-assisted pulsed laser deposition. Thin Solid Films, 2002, 422, 176-179.	0.8	52
224	Growth of N-doped and Ga+N-codoped ZnO films by radical source molecular beam epitaxy. Journal of Crystal Growth, 2002, 237-239, 503-508.	0.7	54
225	Molecular beam epitaxial growth and characterization of CuInSe2 and CuGaSe2 for device applications. Journal of Crystal Growth, 2002, 237-239, 1993-1999.	0.7	23
226	Static analysis of off-axis crystal film growth onto a lattice-mismatched substrate. Applied Physics Letters, 2001, 79, 608-610.	1.5	17
227	Growth of Undoped ZnO Films with Improved Electrical Properties by Radical Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2001, 40, 250-254.	0.8	85
228	Control of Optical and Electrical Properties of ZnO Films for Photovoltaic Applications. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	3
229	Significant Compositional Changes and Formation of a Ga-O Phase after Oxygen-annealing of Ga-rich CuGaSe₂ Films. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	2
230	Observation of Interdiffusion in ZnO/CuInSe2 Heterostructures and its Effect on Film Properties. Materials Research Society Symposia Proceedings, 2001, 668, 1.	0.1	4
231	Anion vacancies in CuInSe2. Thin Solid Films, 2001, 387, 129-134.	0.8	30
232	Optical properties of high-quality CuGaSe2 epitaxial layers examined by piezoelectric photoacoustic spectroscopy. Solar Energy Materials and Solar Cells, 2001, 67, 173-178.	3.0	2
233	Nucleation and growth of ZnO on sapphire substrates using molecular beam epitaxy. Journal of Crystal Growth, 2001, 227-228, 911-916.	0.7	21
234	Growth and characterization of undoped ZnO films for single crystal based device use by radical source molecular beam epitaxy (RS-MBE). Journal of Crystal Growth, 2001, 227-228, 923-928.	0.7	35

#	Article	IF	Citations
235	Photoluminescence properties of sodium incorporation in CuInSe2 and CuIn3Se5 thin films. Solar Energy Materials and Solar Cells, 2001, 67, 289-295.	3.0	24
236	Interactions between gallium and nitrogen dopants in ZnO films grown by radical-source molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 4139-4141.	1.5	132
237	Physics and Chemistry in Physical Vapor Deposition of Cu(In,Ga)Se₂ Thin Films. Japanese Journal of Applied Physics, 2000, 39, 8.	0.8	3
238	Improvement of Electrical Properties in ZnO Thin Films Grown by Radical Source(RS)-MBE. Physica Status Solidi A, 2000, 180, 287-292.	1.7	41
239	ZnO growth on Si by radical source MBE. Journal of Crystal Growth, 2000, 214-215, 50-54.	0.7	116
240	Nitrogen-induced defects in ZnO:N grown on sapphire substrate by gas source MBE. Journal of Crystal Growth, 2000, 209, 526-531.	0.7	152
241	Uniaxial locked growth of high-quality epitaxial ZnO films on -Al2O3. Journal of Crystal Growth, 2000, 209, 532-536.	0.7	85
242	Temperature variation of nonradiative carrier recombination processes in high-quality CuGaSe2 thin films grown by molecular beam epitaxy. Applied Physics Letters, 2000, 77, 259-261.	1.5	11
243	Uniaxial locked epitaxy of ZnO on the a face of sapphire. Applied Physics Letters, 2000, 77, 1801.	1.5	192
244	Control of Intrinsic Defects in CuInSe₂ Films for Device Applications. Japanese Journal of Applied Physics, 2000, 39, 149.	0.8	3
245	A High Resolution X-ray Diffraction and TEM Study of the CuxSe Surface Phase of Cu-rich CuInSe2. Japanese Journal of Applied Physics, 2000, 39, 189.	0.8	2
246	Twin formation in Cu-Ga-Se films grown by molecular beam epitaxy under Ga-excess conditions. Japanese Journal of Applied Physics, 2000, 39, 200.	0.8	3
247	Exciton structures of single- and polycrystalline CuInSe2and CuGaSe2. Japanese Journal of Applied Physics, 2000, 39, 326.	0.8	0
248	Disappearance of the surface Cu-Se second phase during post-growth annealing of CuInSe₂ epitaxial films grown under excess Cu-flux conditions. Japanese Journal of Applied Physics, 2000, 39, 205.	0.8	1
249	Photoluminescence Properties of Sodium Incorporated in CuInSe2 Thin Films. Japanese Journal of Applied Physics, 1999, 38, L289-L291.	0.8	34
250	Effects of Sodium on CuIn3Se5 Thin Films. Japanese Journal of Applied Physics, 1999, 38, L899-L901.	0.8	12
251	Electron Probe Microanalysis of Second Phases via Acceleration Voltage Dependence. Japanese Journal of Applied Physics, 1999, 38, L96-L98.	0.8	6
252	Piezoelectric Photoacoustic and Photoluminescence Properties of CuInXGa1-XSe2Alloys. Japanese Journal of Applied Physics, 1999, 38, 3171-3174.	0.8	7

#	Article	IF	Citations
253	Optical characterizations of CuInSe2 epitaxial layers grown by molecular beam epitaxy. Journal of Applied Physics, 1999, 86, 4354-4359.	1.1	23
254	Effects of the surface Cu2â^'xSe phase on the growth and properties of CuInSe2 films. Applied Physics Letters, 1999, 74, 1630-1632.	1.5	66
255	Epitaxial growth of ZnO thin films on LiNbO3 substrates. Thin Solid Films, 1999, 347, 238-240.	0.8	40
256	Growth of high-quality epitaxial ZnO films on Î±-Al2O3. Journal of Crystal Growth, 1999, 201-202, 627-632.	0.7	173
257	Control of intrinsic defects in molecular beam epitaxy grown CuInSe2. Journal of Crystal Growth, 1999, 201-202, 1061-1064.	0.7	9
258	Growth of LiNbO 3 epitaxial films by oxygen radical-assisted laser molecular beam epitaxy. Applied Physics A: Materials Science and Processing, 1999, 69, S679-S681.	1.1	15
259	Piezoelectric photoacoustic spectra of CuInSe2 thin film grown by molecular beam epitaxy. Thin Solid Films, 1999, 343-344, 591-593.	0.8	3
260	Temperature dependence of photoacoustic spectra in CuInSe2 thin films grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1998, 50, 127-132.	3.0	12
261	Positron Lifetime Study on Semiconductor Thin Films. Materials Science Forum, 1997, 255-257, 714-717.	0.3	5
262	Piezoelectric Photoacoustic Spectra In CuGaSe2 Thin Films Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1997, 485, 151.	0.1	0
263	A shallow state in molecular beam epitaxial grown CuGaSe2film detectable by 1.62 eV photoluminescence. Journal of Applied Physics, 1997, 81, 2794-2798.	1.1	36
264	Linear and nonlinear optical properties of CuInSe2 and CuGaSe2 epitaxial thin films on GaAs(001). Journal of Applied Physics, 1997, 82, 817-824.	1.1	13
265	Effects of strain on the growth and properties of CuInSe2 epitaxial films. Journal of Crystal Growth, 1997, 175-176, 1051-1056.	0.7	4
266	Effects of annealing on CuInSe2 films grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1997, 49, 319-326.	3.0	15
267	Second-harmonic generation from chalcopyrite-structure semiconductor thin films. Optics Letters, 1996, 21, 254.	1.7	8
268	The Effects of Kcn Etching on Cu-Rich Epitaxial CuInSe₂ Thin Films. Materials Research Society Symposia Proceedings, 1996, 426, 213.	0.1	3
269	Growth and Characterization of CuInSe2 Epitaxial Films for Device Applications. Materials Research Society Symposia Proceedings, 1996, 426, 233.	0.1	4
270	The Effects of Air Annealing on Cuinse2 Thin Films Grown by Molecular Beam Fpitaxy. Materials Research Society Symposia Proceedings, 1996, 426, 261.	0.1	0

#	Article	IF	Citations
271	Growth of CuGaSe2 film by molecular beam epitaxy. Microelectronics Journal, 1996, 27, 53-58.	1.1	21
272	Band-edge photoluminescence of CuGaSe2 films grown by molecular beam epitaxy. Journal of Applied Physics, 1996, 79, 4318.	1.1	36
273	Determination of the composition of strained tetragonal epilayers. Applied Physics Letters, 1996, 69, 761-763.	1.5	2
274	High quality CuInSe2 films grown on pseudoâ€latticeâ€matched substrates by molecular beam epitaxy. Applied Physics Letters, 1996, 69, 647-649.	1.5	48
275	Cation sublattice stacking faults in Cu-rich chalcopyrite CuInSe₂. Journal of Materials Research, 1996, 11, 1398-1402.	1.2	2
276	Translational Phase Domains in the Cation Sublattice of Chalcopyrite Compounds. Japanese Journal of Applied Physics, 1996, 35, L843-L845.	0.8	3
277	Defect Structure of Cu-Rich and In-Rich Chalcopyrite CuInSe2 Films Grown on GaAS. Materials Research Society Symposia Proceedings, 1995, 399, 467.	0.1	0
278	Characterization of molecular beam epitaxy grown CuInSe2 on GaAs(001). Journal of Crystal Growth, 1995, 150, 1196-1200.	0.7	15
279	Heteroepitaxy and characterization of CuInSe2 on GaAs(001). Journal of Crystal Growth, 1995, 150, 1201-1205.	0.7	64
280	Excitonic emissions from CuInSe2 on GaAs(001) grown by molecular beam epitaxy. Applied Physics Letters, 1995, 67, 1289-1291.	1.5	53
281	Microstructural Characterization for Sputter-Deposited $f CuInSe_{2}$ Films and Photovoltaic Devices. Japanese Journal of Applied Physics, 1995, 34, 4715-4721.	0.8	19
282	Sharp Optical Emission from $f CuInSe_{2}$ Thin Films Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1994, 33, L500-L502.	0.8	23
283	Photoluminescence properties of CuInSe2 grown by molecular beam epitaxy. Solar Energy Materials and Solar Cells, 1994, 35, 141-147.	3.0	9
284	Polarization-resolved photoluminescence of InAs/GaAs strained-layer structures on variously oriented substrates. Applied Surface Science, 1994, 75, 164-168.	3.1	4
285	Growth control of InAs thin layers on GaAs substrates with several orientations. Applied Surface Science, 1994, 75, 279-284.	3.1	5
286	Annealing effect in InAs/GaAs multiple quantum wells grown on variously oriented substrates. Applied Surface Science, 1993, 68, 251-255.	3.1	1
287	Ion implantation of isoelectronic impurities into InP. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 910-914.	0.6	3
288	Pulsed UV laser irradiation effect for Sn+-implanted GaAs. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 578-582.	0.6	2

#	Article	IF	Citations
289	Properties of Mn+-implanted GaAs. Nuclear Instruments & Methods in Physics Research B, 1993, 80-81, 691-696.	0.6	3
290	The Initial Growth Stage of the InAs Quantum Well Structures on Variously Oriented GaAs Substrates. Japanese Journal of Applied Physics, 1993, 32, 4889-4893.	0.8	4
291	Formation of four new shallow emissions in Mn+ionâ€implanted GaAs grown by molecular beam epitaxy having extremely low concentration of background impurities. Applied Physics Letters, 1993, 63, 1780-1782.	1.5	21
292	Molecular Beam Epitaxial Growth and Properties of CuInSe₂. Japanese Journal of Applied Physics, 1993, 32, 161.	0.8	11
293	Optical Characterization of 100 eV C+ Ion Doped GaAs. Materials Research Society Symposia Proceedings, 1993, 300, 357.	0.1	2
294	Low temperature photoluminescence from GaAs impinged by mass-separated low-energy C⁺ ion beams during molecular beam epitaxy. Materials Research Society Symposia Proceedings, 1993, 316, 1029.	0.1	5
295	Formation of Shallow Energy Levels in Mn+ Implanted GaAs with Extremely Low Background Impurity Concentration. Materials Research Society Symposia Proceedings, 1993, 316, 343.	0.1	0
296	Damage-Free Ion Beam Doping of Carbon During Molecular Beam Epitaxy of GaAs. Materials Research Society Symposia Proceedings, 1993, 316, 965.	0.1	2
297	Electro-optic properties of InGaAs/GaAs multiquantum wells for modulator applications. Electronics Letters, 1992, 28, 1085.	0.5	4
298	Growth and Stability of Strained-Layer Multiple Quantum Wells. Materials Research Society Symposia Proceedings, 1991, 240, 201.	0.1	0
299	Molecular beam epitaxial growth and properties of highly strained InxGa1â^'xAs/GaAs multiple quantum wells. Journal of Crystal Growth, 1991, 111, 419-423.	0.7	3
300	Carrier screening of electric field and electroabsorption saturation in InGaAs-GaAs quantum well structure. Electronics Letters, 1991, 27, 2310.	0.5	6
301	<title>Optimization of strained-layer In<formula><inf><roman>x</roman></inf></formula>Ga<formula><inf><roman>1-x</roman></inf></formula>As/GaAs multiple quantum wells for electroabsorption modulation</title>. , 1990, , .		0
302	Electroabsorption effects in InxGa1â^'xAs/GaAs strainedâ€layer superlattices. Applied Physics Letters, 1990, 56, 475-477.	1.5	6
303	Highly-Strained InxGa1-xAs/GaAs Multiple Quantum Wells for Electroabsorption Modulation. Japanese Journal of Applied Physics, 1990, 29, L1833-L1835.	0.8	2
304	Bandâ€edge discontinuities of strainedâ€layer InxGa1â^'xAs/GaAs heterojunctions and quantum wells. Applied Physics Letters, 1989, 55, 1339-1341.	1.5	98
305	Automatic shutter control for molecularâ€beam epitaxial reactors. Review of Scientific Instruments, 1988, 59, 1246-1247.	0.6	0
306	Simple, inexpensive double ac Hall measurement system for routine semiconductor characterization. Review of Scientific Instruments, 1987, 58, 1764-1766.	0.6	9

#	Article	IF	Citations
307	Efficiency Enhancement of Cu(In,Ga)Se₂Solar Cells Fabricated on Flexible Polyimide Substrates using Alkali-Silicate Glass Thin Layers. Applied Physics Express, 0, 1, 092303.	1.1	37